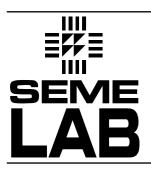
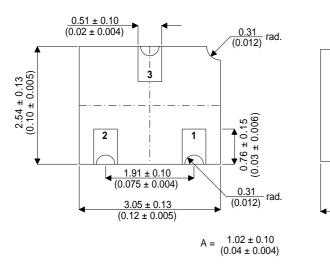
2N2894CSM



HIGH SPEED, MEDIUM POWER, PNP GENERAL PURPOSE TRANSISTOR IN A HERMETICALLY SEALED CERAMIC SURFACE MOUNT PACKAGE FOR HIGH RELIABILITY APPLICATIONS





SOT23 CERAMIC (LCC1 PACKAGE)

Underside View

PAD 1 – Base PAD 2 – Emitter PAD 3 – Collector

FEATURES

- SILICON PLANAR EPITAXIAL PNP TRANSISTOR
- HERMETIC CERAMIC SURFACE MOUNT PACKAGE (SOT23 COMPATIBLE)
- SCREENING OPTIONS AVAILABLE
- HIGH SPEED, LOW SATURATION SWITCH

APPLICATIONS:

Hermetically sealed surface mount version of the popular 2N2894 for high reliability applications requiring small size and low weight devices.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

V _{CBO}	Collector – Base Voltage	-12V			
V _{CEO}	Collector – Emitter Voltage	-12V			
V _{EBO}	Emitter – Base Voltage	-4V			
I _C	Collector Current	200mA			
P _D	Total Device Dissipation @ T _A =25°C	360mW			
	Derate above 25°C	2.06mW / °C			
P _D	Total Device Dissipation @ T _C =25°C	1.2W			
	Derate above 25°C	6.85mW / °C			
T_{STG} , T_{J}	Operating and Storage Temperature Range	–65 to +200°C			

Α

1.40 (0.055)

max.

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.





ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise stated)

	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
V _{(BR)CBO*}	Collector – Base Breakdown Voltage	I _C = 10μΑ	I _E = 0	- 12			
V _{(BR)CEO}	Collector – Emitter Breakdown Voltage	I _C = 10mA	I _B = 0	- 12			V
V _{(BR)EBO}	Emitter – Base Breakdown Voltage	I _E = 10μΑ	$I_{\rm C} = 0$	- 4			
I _{CBO}	Collector Cut-off Current	$V_{CB} = -6V$	T _{amb} = 125°C			- 10	μA
I _{CES}	Collector Cut-off Current	$V_{BE} = 0$	$V_{CE} = -6V$			- 80	nA
V _{CE(sat)}	Collector – Emitter Saturation Voltage	I _C = -10mA	I _B = -1mA			-0.15	V
		I _C = -30mA	I _B = -3mA			-0.20	
		$I_{\rm C} = -100 {\rm mA}$	I _B = -10mA			- 0.50	
V _{BE(sat)}	Base – Emitter On Voltage	I _C = -10mA	$I_B = -1mA$	-0.78		-0.98	V
		I _C = -30mA	I _B = -3mA	-0.85		-1.2	
		$I_{\rm C} = -100 {\rm mA}$	I _B = -10mA			-1.7	
h _{FE}	DC Current Gain	I _C = -10mA	$V_{CE} = -0.3V$	30			
		I _C = -30mA	$V_{CE} = -0.5V$	40		150	
		$I_{\rm C} = -100 {\rm mA}$	$V_{CE} = -1V$	25			
		I _C = –30mA	$V_{CE} = -0.5V$	17			
			T _{amb} = 125°C				
f _T	Current Gain Bandwidth Product	$V_{CE} = -10V$	f = 100MHz	400			MHz
		I _C = –30mA					
C _{ebo}	Emitter – Base – Capacitance	$V_{EB} = -5V$	I _C = 0			6	pF
		f = 1MHz				0	
C _{cbo}	Collector – Base – Capacitance	$V_{CB} = -5V$	I _C = 0			6	pF
		f = 1MHz					
t _{on}	Turn on Time	I _C = -30mA	$V_{CE} = -2V$			60	ns
		$I_{B2} = -1.5 mA$				00	
t _{off}	Turn off Time	I _C = –30mA	$V_{CE} = -2V$			9	ns
		I _{B1} = I _{B2} = -1.5	ōmA				

* Pulse Test: $t_p \leq 300 \mu s, \ \delta \leq 2\%$.

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